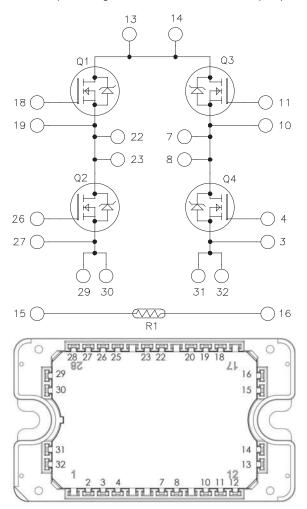
# MSCSM120HM31T3AG

# **Full Bridge SiC MOSFET Power Module**

### **Product Overview**

The MSCSM120HM31T3AG device is a phase leg 1200V, 89A silicon carbide (SiC) MOSFET power module.



#### Notes:

- All multiple inputs and outputs must be shorted together. For example, 13/14, 29/30, 22/23, and so on.
- All ratings at T<sub>J</sub> = 25 °C, unless otherwise specified.

**⚠** CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are key features of the MSCSM120HM31T3AG device:

- SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High temperature performance
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AIN) substrate for improved thermal performance

#### **Benefits**

The following are the benefits of MSCSM120HM31T3AG device:

- · High power and efficiency converters and inverters
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

### **Application**

The MSCSM120HM31T3AG device is designed for the following applications:

- · Welding converters
- Switched mode power supplies
- Uninterruptible power supplies
- EV motor and traction drive

## 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120HM31T3AG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120HM31T3AG device.

**Table 1-1. Absolute Maximum Ratings** 

Symbol	Parameter		Maximum Ratings	Unit	
V <sub>DSS</sub>	Drain-Source voltage	Drain-Source voltage		V	
I <sub>D</sub>	10		89	A	
			71		
I <sub>DM</sub>	Pulsed drain current	Pulsed drain current			
V <sub>GS</sub>	Gate-Source voltage		-10/23	V	
R <sub>DS(on)</sub>	Drain-Source ON resistance		31	mΩ	
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	395	W	

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120HM31T3AG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0V V <sub>DS</sub> = 1200V		_	10	100	μΑ
R <sub>DS(on)</sub>	registance		T <sub>J</sub> = 25 °C	_	25	31	mΩ
			T <sub>J</sub> = 175 °C	_	40	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 3 \text{ mA}$		1.8	2.8	_	V
I <sub>GSS</sub>	Gate–Source leakage current	$V_{GS} = 20V; V_{DS} = 0$	V <sub>GS</sub> = 20V; V <sub>DS</sub> = 0V		_	150	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120HM31T3AG device.

**Table 1-3. Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit	
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0V		_	3020	_	pF	
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 1000V		_	270	_		
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	25	_		
Qg	Total gate charge	V <sub>GS</sub> = -5V/20V		_	232	_	nC	
Q <sub>gs</sub>	Gate-Source charge	V <sub>Bus</sub> = 800V		_	41	_		
$Q_{gd}$	Gate-Drain charge	I <sub>D</sub> = 40A		_	50	_		
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5V/20V		_	30	_	ns	
T <sub>r</sub>	Rise time	V <sub>Bus</sub> = 800V		_	30	_		
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 50A		_	50	_		
T <sub>f</sub>	Fall time	$R_{G(on)} = 8\Omega$ $R_{G(off)} = 4.7\Omega$			25	_		
Eon	Turn-on energy	V <sub>GS</sub> = -5V/20V	T <sub>J</sub> = 150 °C	_	1.2	_	mJ	
E <sub>off</sub>	Turn-off energy	$V_{Bus} = 600V$ $I_D = 50A$ $R_{G(on)} = 8\Omega$ $R_{G(off)} = 4.7\Omega$		_	0.66	_		
R <sub>Gint</sub>	Internal gate resistance			_	0.88	_	Ω	
R <sub>thJC</sub>	Junction-to-case thermal res	sistance		_		0.38	°C/W	

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120HM31T3AG device.

**Table 1-4. Body Diode Ratings and Characteristics** 

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub>	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 40A$	_	4	_	V
		$V_{GS} = -5V; I_{SD} = 40A$	_	4.2	_	
t <sub>rr</sub>	Reverse recovery time	$I_{SD} = 40A; V_{GS} = -5V$	_	90	_	ns
Q <sub>rr</sub>	Reverse recovery charge	$V_R = 800V$ ; $di_F/dt = 1000 A/\mu s$	_	550	_	nC
I <sub>rr</sub>	Reverse recovery current		_	13.5	_	Α

#### 1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120HM31T3AG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristics	Characteristics				Unit
V <sub>ISOL</sub>	RMS isolation voltage, any termi	inal to case t = 1 min,	50 Hz/60 Hz	4000	_	V
T <sub>J</sub>	Operating junction temperature	Operating junction temperature range			175	°C
T <sub>JOP</sub>	Recommended junction tempera	Recommended junction temperature under switching conditions				
T <sub>STG</sub>	Storage temperature range	Storage temperature range				
T <sub>C</sub>	Operating case temperature	Operating case temperature				
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			<u> </u>	110	g

The following table lists the temperature sensor NTC of the MSCSM120HM31T3AG device.

**Table 1-6. Temperature Sensor NTC** 

Symbol	Characteristic		Min.	Тур.	Max.	Unit
R <sub>25</sub>	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_	_	_	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15K	_	_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

### 1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120HM31T3AG device.

Figure 1-1. Maximum Thermal Impedance

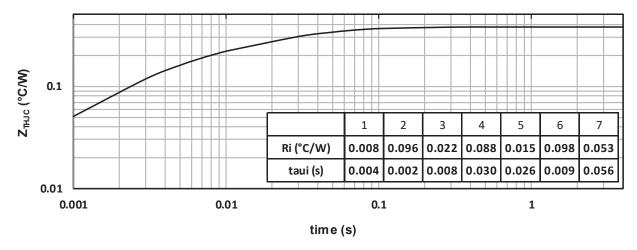


Figure 1-2. Output Characteristics, T<sub>J</sub> = 25 °C

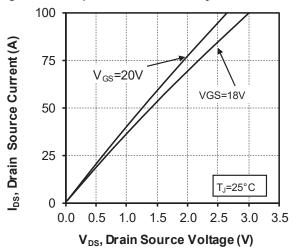


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C

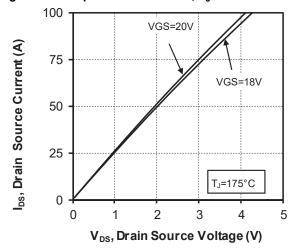


Figure 1-4. Normalized R<sub>DS(on)</sub> vs. Temperature

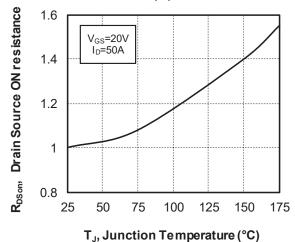


Figure 1-5. Transfer Characteristics

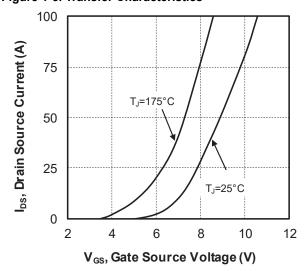


Figure 1-6. Switching Energy vs. Current

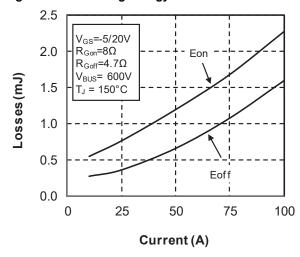


Figure 1-7. Switching Energy vs. Rg

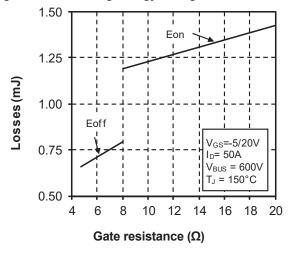


Figure 1-8. Capacitance vs. Drain Source Voltage

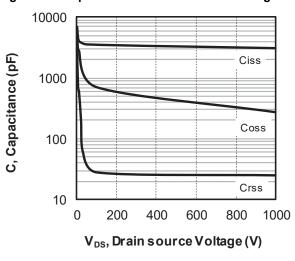


Figure 1-9. Gate Charge vs. Gate Source Voltage

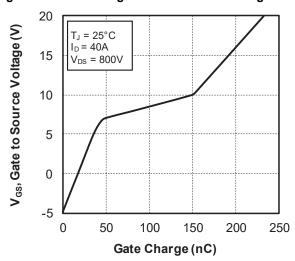


Figure 1-10. Body Diode Characteristics, T<sub>J</sub> = 25 °C

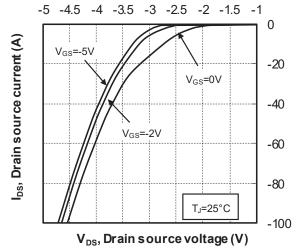


Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 25 °C

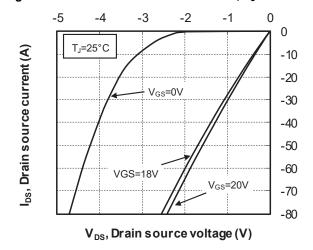
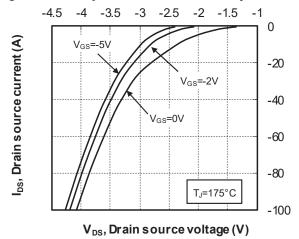
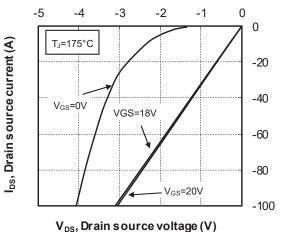
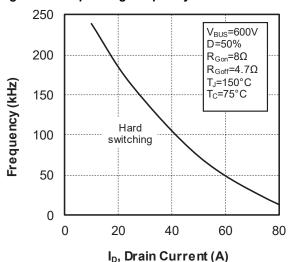


Figure 1-12. Body Diode Characteristics, T<sub>J</sub> = 175 °C Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 175 °C







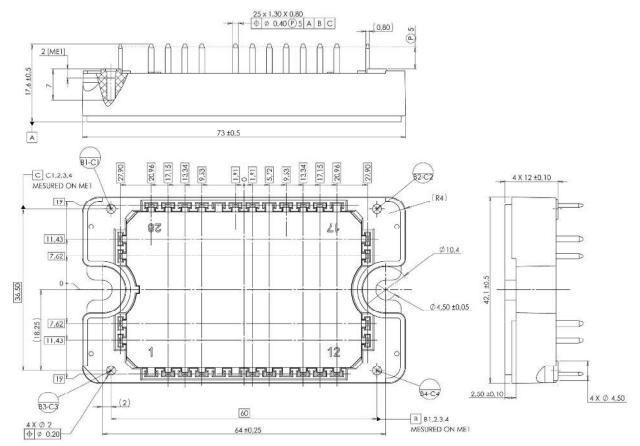
## 2. Package Specifications

The following section shows the package specification of the MSCSM120HM31T3AG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120HM31T3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information.

## MSCSM120HM31T3AG

**Revision History** 

# 3. Revision History

Revision	Date	Description
Α	06/2022	Initial Release

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